ABSTRACT

There is disclosed a single crystal obtained by a single crystal pulling method, wherein an interval of striations incorporated into the single crystal due to temperature fluctuation of crystal melt at the time of crystal growth is controlled, and a method of growing a single crystal according to a single crystal pulling method, wherein a growth rate and/or a temperature fluctuation period are controlled so that $V \times F / \sin\theta$ may be in a certain range when a growth rate at the time of growing a single crystal is defined as V (mm/min), a temperature fluctuation period of crystal melt is defined as F (min), and an angle to the level surface of a crystal-growth interface is defined as θ. Thereby nanotopology characteristics can be improved from aspects different from the processing conditions of the surface of the wafer and there can be provided a single crystal which can produce a wafer excellent in nanotopology characteristics, especially in nanotopology characteristics measured in 2 mm x 2 mm square, and a method of growing a single crystal for growing the single crystal.